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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, Ethernet, I ² C, IrDA, LINbus, Memory Card, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	140
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	132K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	201-UF BGA
Supplier Device Package	176+25UF BGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f217ieh6

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Table 2. STM32F215xx and STM32F217xx: features and peripheral counts

Peripherals		STM32F215Rx		STM32F215Vx		STM32F215Zx		STM32F217Vx		STM32F217Zx		STM32F217Ix	
Flash memory in Kbytes		512	1024	512	1024	512	1024	512	1024	512	1024	512	1024
SRAM in Kbytes	System	128(112+16)											
	Backup	4		4		4		4		4		4	
FSMC memory controller		No		Yes ⁽¹⁾									
Ethernet ⁽²⁾		No						Yes					
Timers	General-purpose	10											
	Advanced-control	2											
	Basic	2											
	IWDG	Yes											
	WWDG	Yes											
RTC		Yes											
Random number generator		Yes											
Communication interfaces	SPI / (I ² S)	3/(2) ⁽³⁾											
	I ² C	3											
	USART	4											
	UART	2											
	USB OTG FS	Yes											
	USB OTG HS	Yes											
	CAN	2											
Camera interface ⁽²⁾		No						Yes					
Encryption		Yes											
GPIOs		51		82		114		82		114		140	
SDIO		Yes											
12-bit ADC		3											
Number of channels		16		16		24		16		24		24	
12-bit DAC		Yes											
Number of channels		2											
Maximum CPU frequency		120 MHz											
Operating voltage		1.8 V to 3.6 V											

3.4 Embedded Flash memory

The STM32F21x devices embed a 128-bit wide Flash memory of 128 Kbytes, 256 Kbytes, 512 Kbytes, 768 Kbytes or 1 Mbyte available for storing programs and data.

The devices also feature 512 bytes of OTP memory that can be used to store critical user data such as Ethernet MAC addresses or cryptographic keys.

3.5 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a software signature during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.6 Embedded SRAM

All STM32F21x products embed:

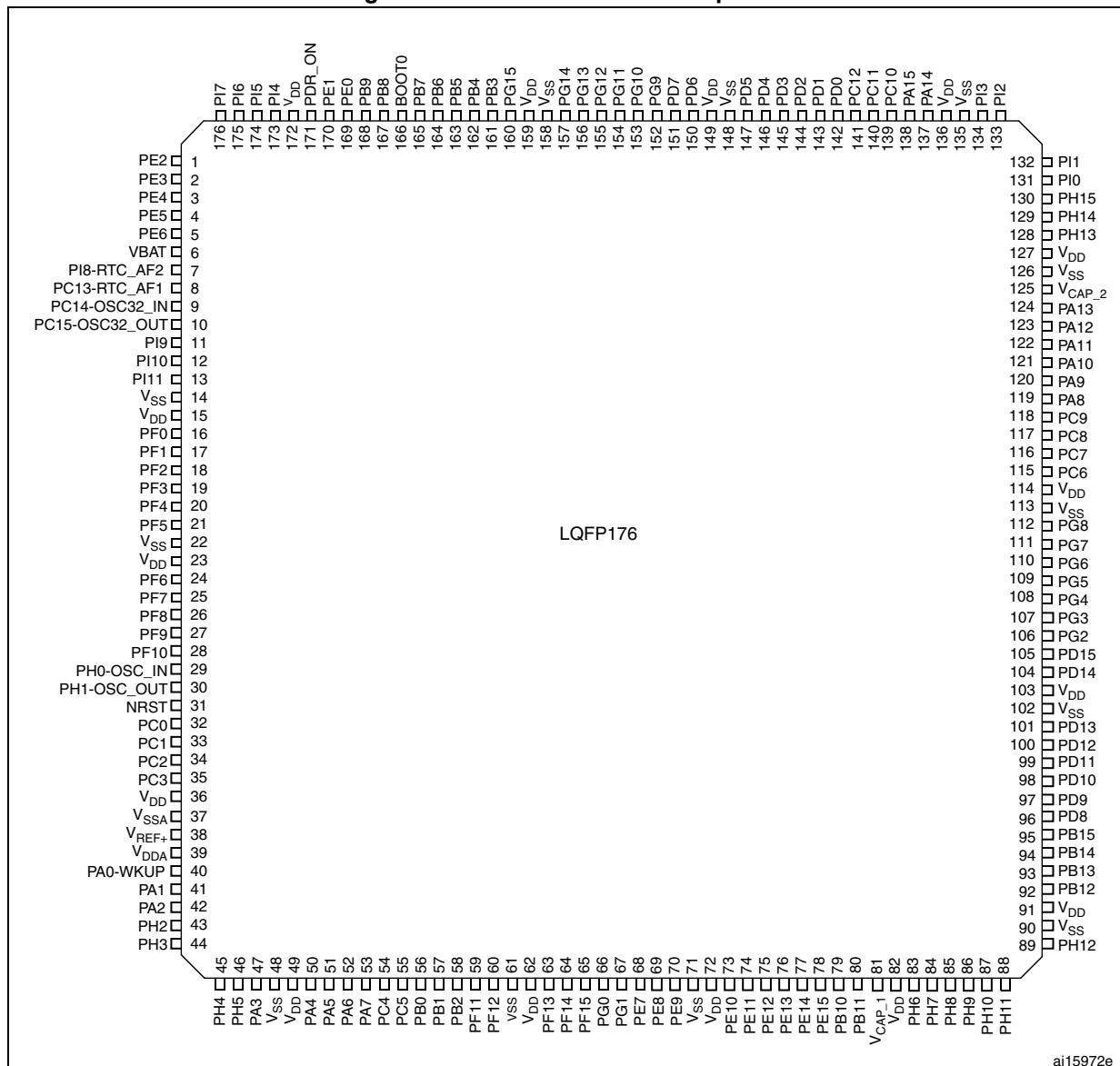
- Up to 128 Kbytes of system SRAM accessed (read/write) at CPU clock speed with 0 wait states
- 4 Kbytes of backup SRAM.

The content of this area is protected against possible unwanted write accesses, and is retained in Standby or VBAT mode.

3.7 Multi-AHB bus matrix

The 32-bit multi-AHB bus matrix interconnects all the masters (CPU, DMAs, Ethernet, USB HS) and the slaves (Flash memory, RAM, FSMC, AHB and APB peripherals) and ensures a seamless and efficient operation even when several high-speed peripherals work simultaneously.

Figure 12. STM32F21x LQFP176 pinout



ai15972e

1. RFU means "reserved for future use". This pin can be tied to V_{DD}, V_{SS} or left unconnected.
2. The above figure shows the package top view.

Table 7. STM32F21x pin and ball definitions

Pins					Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Note	Alternate functions	Additional functions
LQFP64	LQFP100	LQFP144	LQFP176	UFBGA176						
-	1	1	1	A2	PE2	I/O	FT	-	TRACECLK, FSMC_A23, ETH_MII_TXD3, EVENTOUT	-
-	2	2	2	A1	PE3	I/O	FT	-	TRACED0, FSMC_A19, EVENTOUT	-
-	3	3	3	B1	PE4	I/O	FT	-	TRACED1, FSMC_A20, DCMI_D4/ EVENTOUT	-
-	4	4	4	B2	PE5	I/O	FT	-	TRACED2, FSMC_A21, TIM9_CH1, DCMI_D6, EVENTOUT	-
-	5	5	5	B3	PE6	I/O	FT	-	TRACED3, FSMC_A22, TIM9_CH2, DCMI_D7, EVENTOUT	-
1	6	6	6	C1	V _{BAT}	S	-	-	-	-
-	-	-	7	D2	PI8	I/O	FT	(2)(3)	EVENTOUT	RTC_AF2
2	7	7	8	D1	PC13	I/O	FT	(2)(3)	EVENTOUT	RTC_AF1
3	8	8	9	E1	PC14/OSC32_IN (PC14)	I/O	FT	(2)(3)	EVENTOUT	OSC32_IN ⁽⁴⁾
4	9	9	10	F1	PC15/ OSC32_OUT (PC15)	I/O	FT	(2)(3)	EVENTOUT	OSC32_OUT ⁽⁴⁾
-	-	-	11	D3	PI9	I/O	FT	-	CAN1_RX, EVENTOUT	-
-	-	-	12	E3	PI10	I/O	FT	-	ETH_MII_RX_ER, EVENTOUT	-
-	-	-	13	E4	PI11	I/O	FT	-	OTG_HS_ULPI_DIR, EVENTOUT	-
-	-	-	14	F2	V _{SS}	S	-	-	-	-
-	-	-	15	F3	V _{DD}	S	-	-	-	-
-	-	10	16	E2	PF0	I/O	FT	-	FSMC_A0, I2C2_SDA, EVENTOUT	-
-	-	11	17	H3	PF1	I/O	FT	-	FSMC_A1, I2C2_SCL, EVENTOUT	-
-	-	12	18	H2	PF2	I/O	FT	-	FSMC_A2, I2C2_SMBA, EVENTOUT	-
-	-	13	19	J2	PF3	I/O	FT	(4)	FSMC_A3, EVENTOUT	ADC3_IN9

Table 7. STM32F21x pin and ball definitions (continued)

Pins					Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Note	Alternate functions	Additional functions
LQFP64	LQFP100	LQFP144	LQFP176	UFBGA176						
38	64	97	116	G15	PC7	I/O	FT	-	I2S3_MCK, TIM8_CH2,SDIO_D7, USART6_RX, DCMI_D1,TIM3_CH2, EVENTOUT	-
39	65	98	117	G14	PC8	I/O	FT	-	TIM8_CH3,SDIO_D0, TIM3_CH3, USART6_CK, DCMI_D2, EVENTOUT	-
40	66	99	118	F14	PC9	I/O	FT	-	I2S2_CKIN, I2S3_CKIN, MCO2, TIM8_CH4,SDIO_D1, I2C3_SDA, DCMI_D3, TIM3_CH4, EVENTOUT	-
41	67	100	119	F15	PA8	I/O	FT	-	MCO1, USART1_CK, TIM1_CH1, I2C3_SCL, OTG_FS_SOF, EVENTOUT	-
42	68	101	120	E15	PA9	I/O	FT	-	USART1_TX, TIM1_CH2, I2C3_SMBA, DCMI_D0, EVENTOUT	OTG_FS_ VBUS
43	69	102	121	D15	PA10	I/O	FT	-	USART1_RX, TIM1_CH3, OTG_FS_ID,DCMI_D1, EVENTOUT	-
44	70	103	122	C15	PA11	I/O	FT	-	USART1_CTS, CAN1_RX, TIM1_CH4, OTG_FS_DM, EVENTOUT	-
45	71	104	123	B15	PA12	I/O	FT	-	USART1_RTS, CAN1_TX, TIM1_ETR, OTG_FS_DP, EVENTOUT	-
46	72	105	124	A15	PA13 (JTMS-SWDIO)	I/O	FT	-	JTMS-SWDIO, EVENTOUT	-
47	73	106	125	F13	V _{CAP_2}	S	-	-	-	-
-	74	107	126	F12	V _{SS}	S	-	-	-	-
48	75	108	127	G13	V _{DD}	S	-	-	-	-
-	-	-	128	E12	PH13	I/O	FT	-	TIM8_CH1N, CAN1_TX, EVENTOUT	-
-	-	-	129	E13	PH14	I/O	FT	-	TIM8_CH2N, DCMI_D4, EVENTOUT	-

Table 7. STM32F21x pin and ball definitions (continued)

Pins					Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Note	Alternate functions	Additional functions
LQFP64	LQFP100	LQFP144	LQFP176	UFBGA176						
54	83	116	144	D12	PD2	I/O	FT	-	TIM3_ETR, UART5_RX, SDIO_CMD, DCMI_D11, EVENTOUT	-
-	84	117	145	D11	PD3	I/O	FT	-	FSMC_CLK, USART2_CTS, EVENTOUT	-
-	85	118	146	D10	PD4	I/O	FT	-	FSMC_NOE, USART2_RTS, EVENTOUT	-
-	86	119	147	C11	PD5	I/O	FT	-	FSMC_NWE, USART2_TX, EVENTOUT	-
-	-	120	148	D8	V _{SS}	S		-	-	-
-	-	121	149	C8	V _{DD}	S		-	-	-
-	87	122	150	B11	PD6	I/O	FT	-	FSMC_NWAIT, USART2_RX, EVENTOUT	-
-	88	123	151	A11	PD7	I/O	FT	-	USART2_CK, FSMC_NE1, FSMC_NCE2, EVENTOUT	-
-	-	124	152	C10	PG9	I/O	FT	-	USART6_RX, FSMC_NE2, FSMC_NCE3, EVENTOUT	-
-	-	125	153	B10	PG10	I/O	FT	-	FSMC_NCE4_1, FSMC_NE3, EVENTOUT	-
-	-	126	154	B9	PG11	I/O	FT	-	FSMC_NCE4_2, ETH_MII_TX_EN, ETH_RMII_TX_EN, EVENTOUT	-
-	-	127	155	B8	PG12	I/O	FT	-	FSMC_NE4, USART6_RTS, EVENTOUT	-
-	-	128	156	A8	PG13	I/O	FT	-	FSMC_A24, USART6_CTS, ETH_MII_TXD0, ETH_RMII_TXD0, EVENTOUT	-
-	-	129	157	A7	PG14	I/O	FT	-	FSMC_A25, USART6_TX, ETH_MII_TXD1, ETH_RMII_TXD1, EVENTOUT	-
-	-	130	158	D7	V _{SS}	S	-	-	-	-
-	-	131	159	C7	V _{DD}	S	-	-	-	-

Table 18. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{BOR2}	Brownout level 2 threshold	Falling edge	2.44	2.50	2.56	V
		Rising edge	2.53	2.59	2.63	V
V_{BOR3}	Brownout level 3 threshold	Falling edge	2.75	2.83	2.88	V
		Rising edge	2.85	2.92	2.97	V
$V_{BORhyst}^{(1)}$	BOR hysteresis	-	-	100	-	mV
$T_{RSTTEMPO}^{(1)(2)}$	Reset temporization	-	0.5	1.5	3.0	ms
$I_{RUSH}^{(1)}$	InRush current on voltage regulator power-on (POR or wakeup from Standby)	-	-	160	200	mA
$E_{RUSH}^{(1)}$	InRush energy on voltage regulator power-on (POR or wakeup from Standby)	$V_{DD} = 1.8\text{ V}$, $T_A = 105\text{ }^{\circ}\text{C}$, $I_{RUSH} = 171\text{ mA}$ for $31\text{ }\mu\text{s}$	-	-	5.4	μC

1. Guaranteed by design, not tested in production.

2. The reset temporization is measured from the power-on (POR reset or wakeup from V_{BAT}) to the instant when first instruction is read by the user application code.

6.3.6 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in [Figure 18: Current consumption measurement scheme](#).

All Run mode current consumption measurements given in this section are performed using CoreMark[®] code.

Figure 23. Typical current consumption vs. temperature, Run mode, code with data processing running from Flash, ART accelerator OFF, peripherals ON

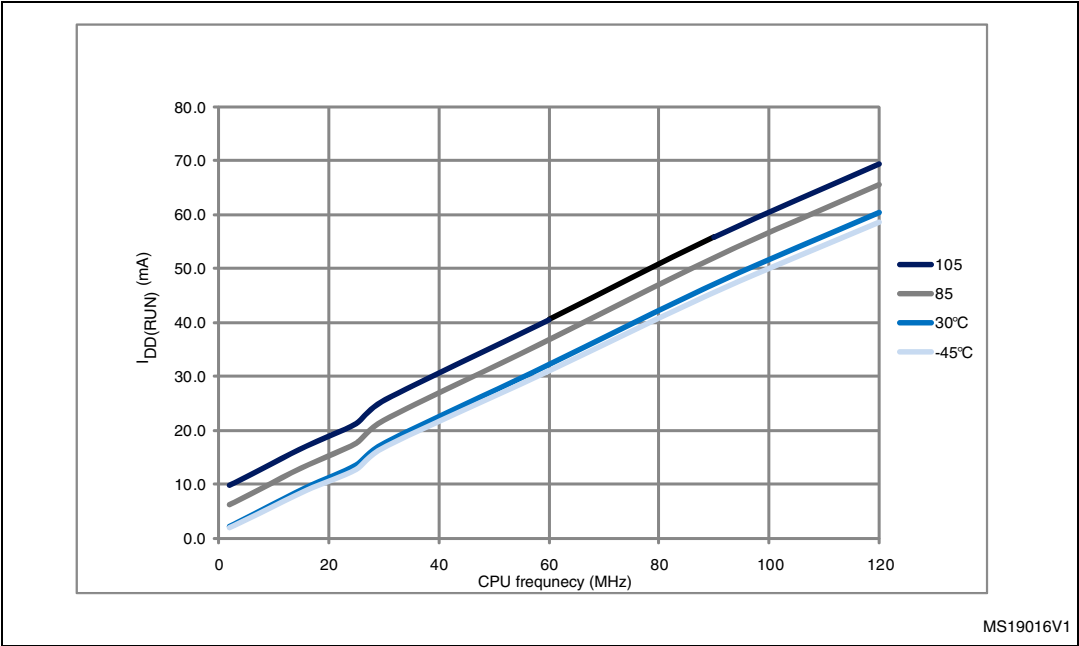


Figure 24. Typical current consumption vs. temperature, Run mode, code with data processing running from Flash, ART accelerator OFF, peripherals OFF

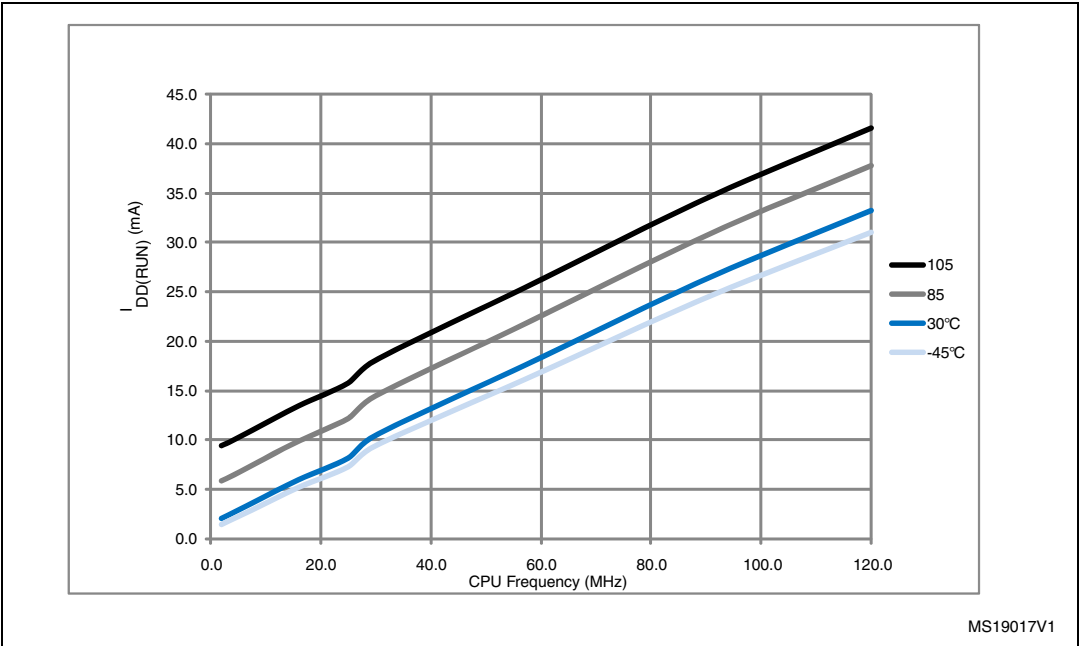
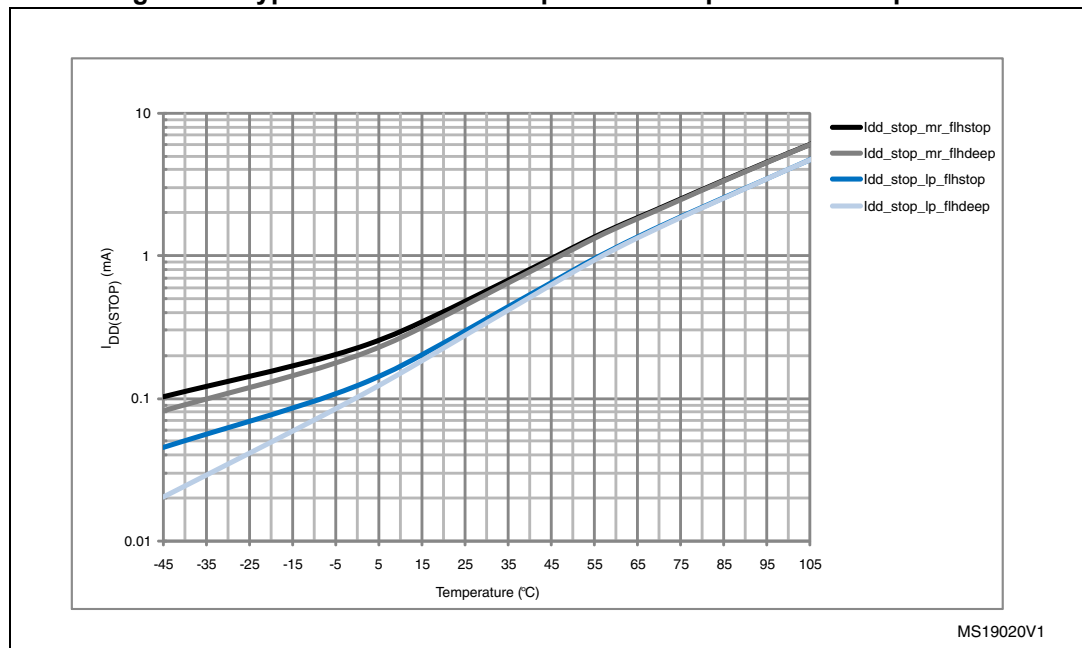


Table 22. Typical and maximum current consumptions in Stop mode

Symbol	Parameter	Conditions	Typ	Max				Unit
			T _A = 25 °C	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C		
I _{DD_STOP}	Supply current in Stop mode with main regulator in Run mode	Flash in Stop mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.55	1.2	11.00	20.00	mA	
		Flash in Deep power down mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.50	1.2	11.00	20.00		
	Supply current in Stop mode with main regulator in Low-power mode	Flash in Stop mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.35	1.1	8.00	15.00		
		Flash in Deep power down mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.30	1.1	8.00	15.00		

Figure 27. Typical current consumption vs. temperature in Stop mode



1. All typical and maximum values from table 18 and figure 26 will be reduced over time by up to 50% as part of ST continuous improvement of test procedures. New versions of the datasheet will be released to reflect these changes

Table 23. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions	Typ			Max ⁽¹⁾		Unit
			T _A = 25 °C			T _A = 85 °C	T _A = 105 °C	
			V _{DD} = 1.8 V	V _{DD} = 2.4 V	V _{DD} = 3.3 V	V _{DD} = 3.6 V		
I _{DD_STBY}	Supply current in Standby mode	Backup SRAM ON, low-speed oscillator and RTC ON	3.0	3.4	4.0	15.1	25.8	μA
		Backup SRAM OFF, low-speed oscillator and RTC ON	2.4	2.7	3.3	12.4	20.5	
		Backup SRAM ON, RTC OFF	2.4	2.6	3.0	12.5	24.8	
		Backup SRAM OFF, RTC OFF	1.7	1.9	2.2	9.8	19.2	

1. Guaranteed by characterization results, not tested in production.

Table 24. Typical and maximum current consumptions in V_{BAT} mode

Symbol	Parameter	Conditions	Typ			Max ⁽¹⁾		Unit
			T _A = 25 °C			T _A = 85 °C	T _A = 105 °C	
			V _{DD} = 1.8 V	V _{DD} = 2.4 V	V _{DD} = 3.3 V	V _{DD} = 3.6 V		
I _{DD_VBAT}	Backup domain supply current	Backup SRAM ON, low-speed oscillator and RTC ON	1.29	1.42	1.68	12	19	μA
		Backup SRAM OFF, low-speed oscillator and RTC ON	0.62	0.73	0.96	8	10	
		Backup SRAM ON, RTC OFF	0.79	0.81	0.86	9	16	
		Backup SRAM OFF, RTC OFF	0.10	0.10	0.10	5	7	

1. Guaranteed by characterization results, not tested in production.

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in [Table 25](#). The MCU is placed under the following conditions:

- At startup, all I/O pins are configured as analog inputs by firmware.
- All peripherals are disabled unless otherwise mentioned
- The given value is calculated by measuring the current consumption
 - with all peripherals clocked off
 - with one peripheral clocked on (with only the clock applied)
- The code is running from Flash memory and the Flash memory access time is equal to 3 wait states at 120 MHz
- Prefetch and Cache ON
- When the peripherals are enabled, HCLK = 120MHz, f_{PCLK1} = f_{HCLK}/4, and f_{PCLK2} = f_{HCLK}/2
- The typical values are obtained for V_{DD} = 3.3 V and T_A = 25 °C, unless otherwise specified.

6.3.8 External clock source characteristics

High-speed external user clock generated from an external source

The characteristics given in [Table 27](#) result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 13](#).

Table 27. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	External user clock source frequency ⁽¹⁾	-	1	-	26	MHz
V_{HSEH}	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSE)}$ $t_{f(HSE)}$	OSC_IN high or low time ⁽¹⁾		5	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time ⁽¹⁾		-	-	20	
$C_{in(HSE)}$	OSC_IN input capacitance ⁽¹⁾	-	-	5	-	pF
$DuCy_{(HSE)}$	Duty cycle	-	45	-	55	%
I_L	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	± 1	μA

1. Guaranteed by design, not tested in production.

Low-speed external user clock generated from an external source

The characteristics given in [Table 28](#) result from tests performed using an low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 13](#).

Table 28. Low-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User External clock source frequency ⁽¹⁾	-	-	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{LSEL}	OSC32_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(LSE)}$ $t_{f(LSE)}$	OSC32_IN high or low time ⁽¹⁾		450	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time ⁽¹⁾		-	-	50	
$C_{in(LSE)}$	OSC32_IN input capacitance ⁽¹⁾	-	-	5	-	pF
$DuCy_{(LSE)}$	Duty cycle	-	30	-	70	%
I_L	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	± 1	μA

1. Guaranteed by design, not tested in production.

Table 33. Main PLL characteristics (continued)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Jitter ⁽³⁾	Cycle-to-cycle jitter	System clock 120 MHz	RMS	-	25	-	ps
			peak to peak	-	±150	-	
	Period Jitter		RMS	-	15	-	
			peak to peak	-	±200	-	
	Main clock output (MCO) for RMII Ethernet	Cycle to cycle at 50 MHz on 1000 samples	-	32	-		
	Main clock output (MCO) for MII Ethernet	Cycle to cycle at 25 MHz on 1000 samples	-	40	-		
	Bit Time CAN jitter	Cycle to cycle at 1 MHz on 1000 samples	-	330	-		
I _{DD(PLL)} ⁽⁴⁾	PLL power consumption on VDD	VCO freq = 192 MHz VCO freq = 432 MHz		0.15 0.45	-	0.40 0.75	mA
I _{DDA(PLL)} ⁽⁴⁾	PLL power consumption on VDDA	VCO freq = 192 MHz VCO freq = 432 MHz		0.30 0.55	-	0.40 0.85	mA

1. Take care of using the appropriate division factor M to obtain the specified PLL input clock values. The M factor is shared between PLL and PLLI2S.
2. Guaranteed by design, not tested in production.
3. The use of 2 PLLs in parallel could degraded the Jitter up to +30%.
4. Guaranteed by characterization results, not tested in production.

Table 34. PLLI2S (audio PLL) characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f _{PLLI2S_IN}	PLLI2S input clock ⁽¹⁾	-	0.95 ⁽²⁾	1	2.10 ⁽²⁾	MHz
f _{PLLI2S_OUT}	PLLI2S multiplier output clock	-	-	-	216	MHz
f _{VCO_OUT}	PLLI2S VCO output	-	192	-	432	MHz
t _{LOCK}	PLLI2S lock time	VCO freq = 192 MHz	75	-	200	µs
		VCO freq = 432 MHz	100	-	300	

Table 34. PLLI2S (audio PLL) characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Jitter ⁽³⁾	Master I2S clock jitter	Cycle to cycle at 12.288 MHz on 48KHz period, N=432, R=5	RMS	-	90	-
			peak to peak	-	±280	-
		Average frequency of 12.288 MHz N=432, R=5 on 1000 samples	-	90	-	ps
	WS I2S clock jitter	Cycle to cycle at 48 KHz on 1000 samples	-	400	-	ps
$I_{DD(PLLI2S)}$ ⁽⁴⁾	PLLI2S power consumption on V_{DD}	VCO freq = 192 MHz VCO freq = 432 MHz	0.15 0.45	-	0.40 0.75	mA
$I_{DDA(PLLI2S)}$ ⁽⁴⁾	PLLI2S power consumption on V_{DDA}	VCO freq = 192 MHz VCO freq = 432 MHz	0.30 0.55	-	0.40 0.85	mA

1. Take care of using the appropriate division factor M to have the specified PLL input clock values.
2. Guaranteed by design, not tested in production.
3. Value given with main PLL running.
4. Guaranteed by characterization results, not tested in production.

Table 50. Characteristics of TIMx connected to the APB2 domain⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
t _{res(TIM)}	Timer resolution time	AHB/APB2 prescaler distinct from 1, f _{TIMxCLK} = 120 MHz	1	-	t _{TIMxCLK}
			8.3	-	ns
		AHB/APB2 prescaler = 1, f _{TIMxCLK} = 60 MHz	1	-	t _{TIMxCLK}
			16.7	-	ns
f _{EXT}	Timer external clock frequency on CH1 to CH4	f _{TIMxCLK} = 120 MHz APB2 = 60 MHz	0	f _{TIMxCLK} /2	MHz
			0	60	MHz
Res _{TIM}	Timer resolution		-	16	bit
t _{COUNTER}	16-bit counter clock period when internal clock is selected		1	65536	t _{TIMxCLK}
			0.0083	546	μs
t _{MAX_COUNT}	Maximum possible count		-	65536 × 65536	t _{TIMxCLK}
			-	35.79	s

1. TIMx is used as a general term to refer to the TIM1, TIM8, TIM9, TIM10, and TIM11 timers.

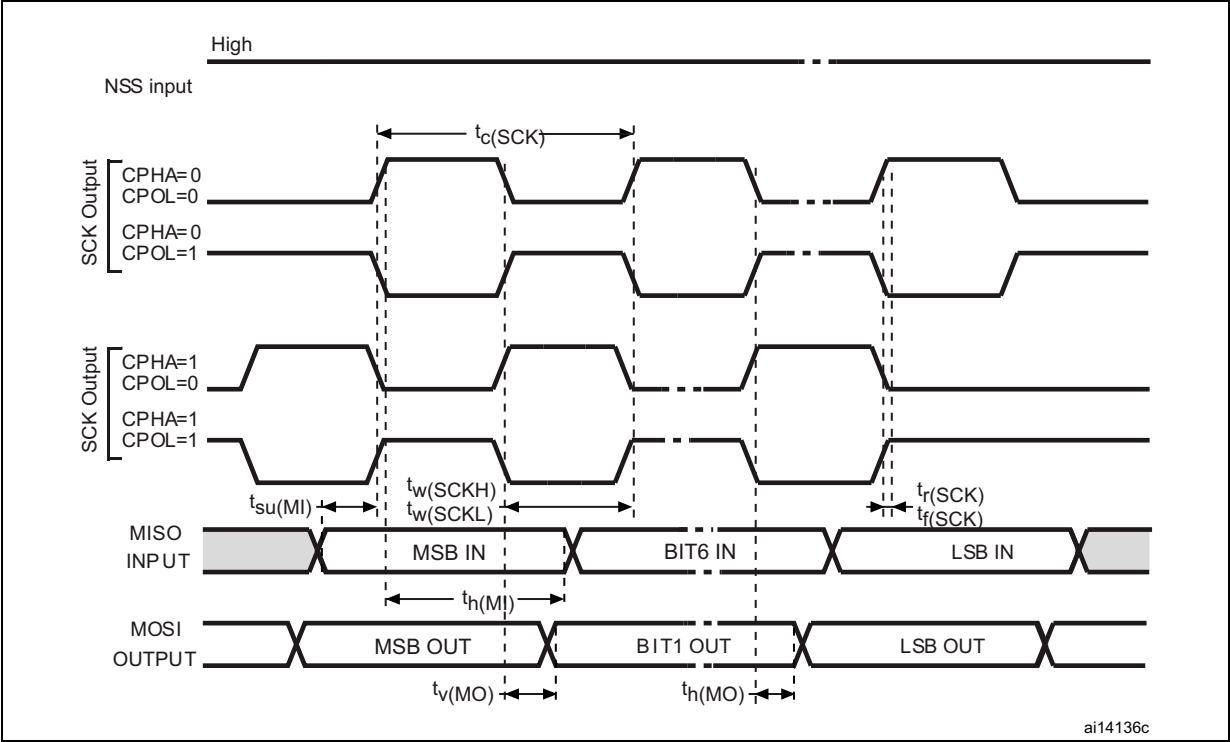
6.3.19 Communications interfaces

I²C interface characteristics

STM32F215xx and STM32F217xx I²C interface meets the requirements of the standard I²C communication protocol with the following restrictions: the I/O pins SDA and SCL are mapped to are not “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

The I²C characteristics are described in [Table 51](#). Refer also to [Section 6.3.16: I/O port characteristics](#) for more details on the input/output alternate function characteristics (SDA and SCL).

Figure 42. SPI timing diagram - master mode



USB OTG FS characteristics

The USB OTG interface is USB-IF certified (Full-Speed). This interface is present in both the USB OTG HS and USB OTG FS controllers.

Table 55. USB OTG FS startup time

Symbol	Parameter	Max	Unit
$t_{\text{STARTUP}}^{(1)}$	USB OTG FS transceiver startup time	1	μs

1. Guaranteed by design, not tested in production.

Table 56. USB OTG FS DC electrical characteristics

Symbol		Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
Input levels	V _{DD}	USB OTG FS operating voltage		3.0 ⁽²⁾	-	3.6	V
	V _{DI} ⁽³⁾	Differential input sensitivity	I(USB_FS_DP/DM, USB_HS_DP/DM)	0.2	-	-	V
	V _{CM} ⁽³⁾	Differential common mode range	Includes V _{DI} range	0.8	-	2.5	
	V _{SE} ⁽³⁾	Single ended receiver threshold		1.3	-	2.0	
Output levels	V _{OL}	Static output level low	R _L of 1.5 kΩ to 3.6 V ⁽⁴⁾	-	-	0.3	V
	V _{OH}	Static output level high	R _L of 15 kΩ to V _{SS} ⁽⁴⁾	2.8	-	3.6	
R _{PD}		PA11, PA12, PB14, PB15 (USB_FS_DP/DM, USB_HS_DP/DM)	V _{IN} = V _{DD}	17	21	24	kΩ
		PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)		0.65	1.1	2.0	
R _{PU}		PA12, PB15 (USB_FS_DP, USB_HS_DP)	V _{IN} = V _{SS}	1.5	1.8	2.1	
		PA9, PB13 (OTG_FS_VBUS, OTG_HS_VBUS)	V _{IN} = V _{SS}	0.25	0.37	0.55	

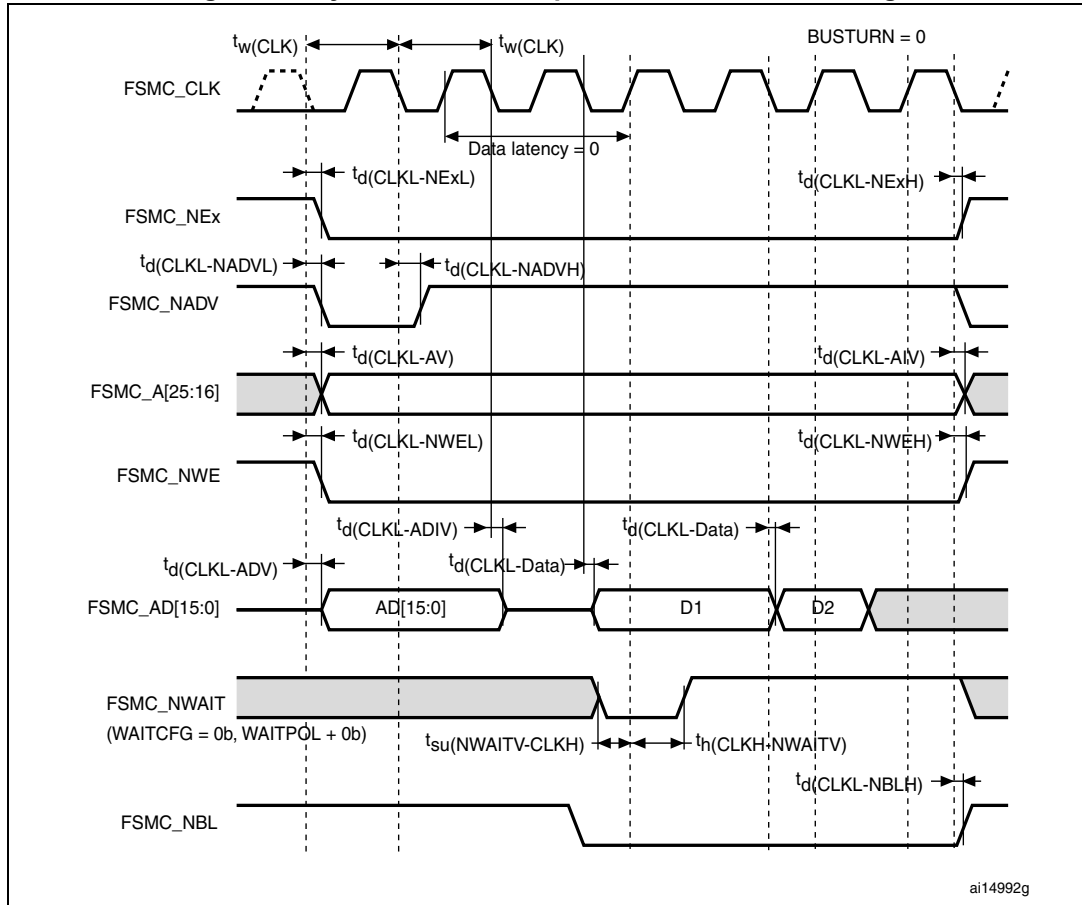
1. All the voltages are measured from the local ground potential.
2. The STM32F215xx and STM32F217xx USB OTG FS functionality is ensured down to 2.7 V but not the full USB OTG FS electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
3. Guaranteed by design, not tested in production.
4. R_{L} is the load connected on the USB OTG FS drivers

Table 75. Synchronous multiplexed NOR/PSRAM read timings⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Min	Max	Unit
$t_{su}(ADV-CLKH)$	FSMC_A/D[15:0] valid data before FSMC_CLK high	5	-	ns
$t_h(CLKH-ADV)$	FSMC_A/D[15:0] valid data after FSMC_CLK high	0	-	ns

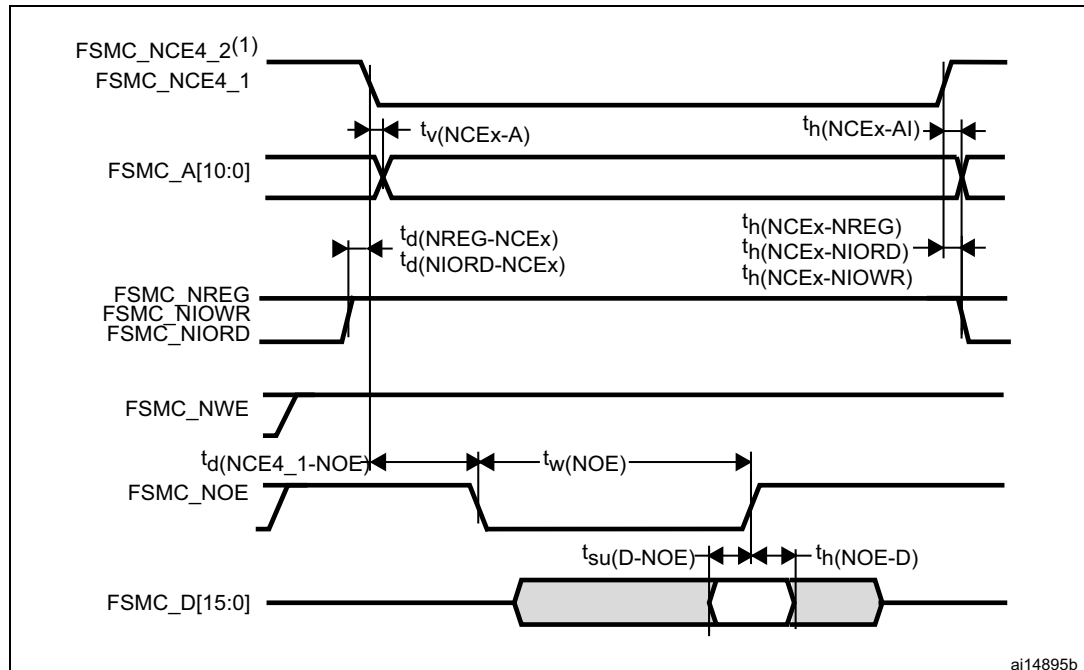
1. $C_L = 30$ pF.

2. Guaranteed by characterization results, not tested in production.

Figure 60. Synchronous multiplexed PSRAM write timings**Table 76. Synchronous multiplexed PSRAM write timings⁽¹⁾⁽²⁾**

Symbol	Parameter	Min	Max	Unit
$t_w(CLK)$	FSMC_CLK period	$2T_{HCLK} - 1$	-	ns
$t_d(CLKL-NExL)$	FSMC_CLK low to FSMC_NEx low (x=0..2)	-	0	ns
$t_d(CLKL-NExH)$	FSMC_CLK low to FSMC_NEx high (x= 0..2)	2	-	ns
$t_d(CLKL-NADVL)$	FSMC_CLK low to FSMC_NADV low	-	2	ns
$t_d(CLKL-NADVH)$	FSMC_CLK low to FSMC_NADV high	3	-	ns
$t_d(CLKL-AV)$	FSMC_CLK low to FSMC_Ax valid (x=16...25)	-	0	ns
$t_d(CLKL-AIV)$	FSMC_CLK low to FSMC_Ax invalid (x=16...25)	7	-	ns

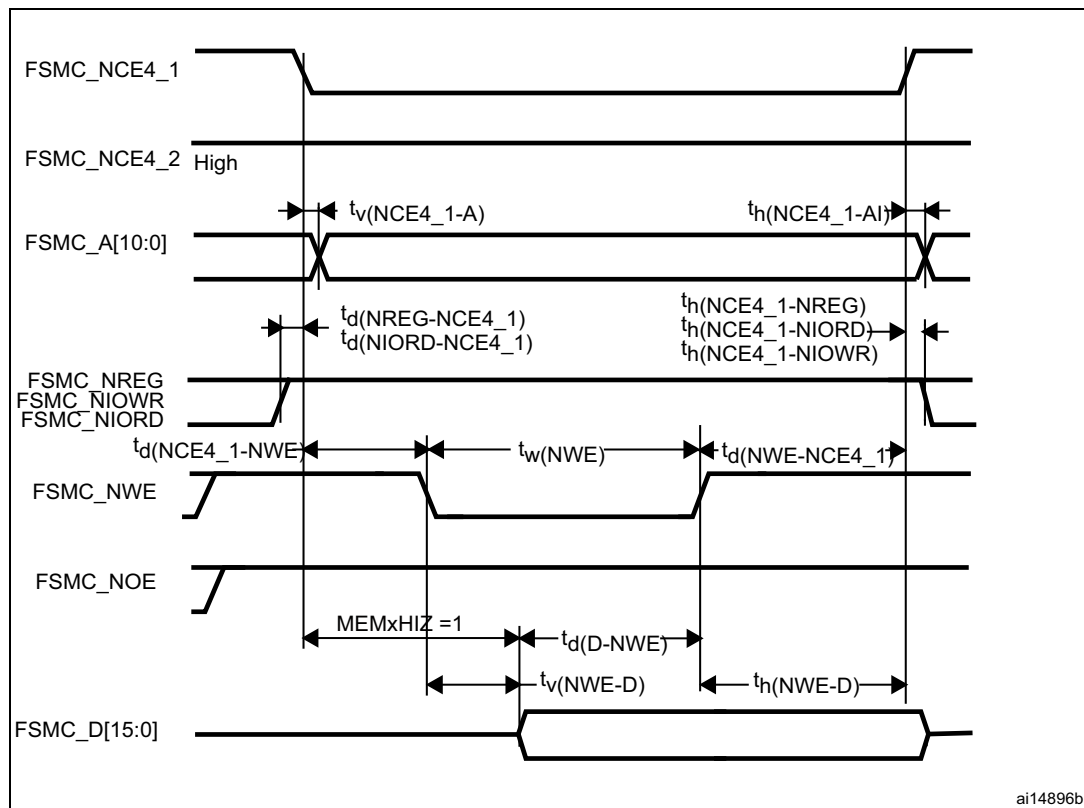
Figure 63. PC Card/CompactFlash controller waveforms for common memory read access



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1. FSMC_NCE4_2 remains high (inactive during 8-bit access).

Figure 64. PC Card/CompactFlash controller waveforms for common memory write access



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Figure 69. NAND controller waveforms for read access

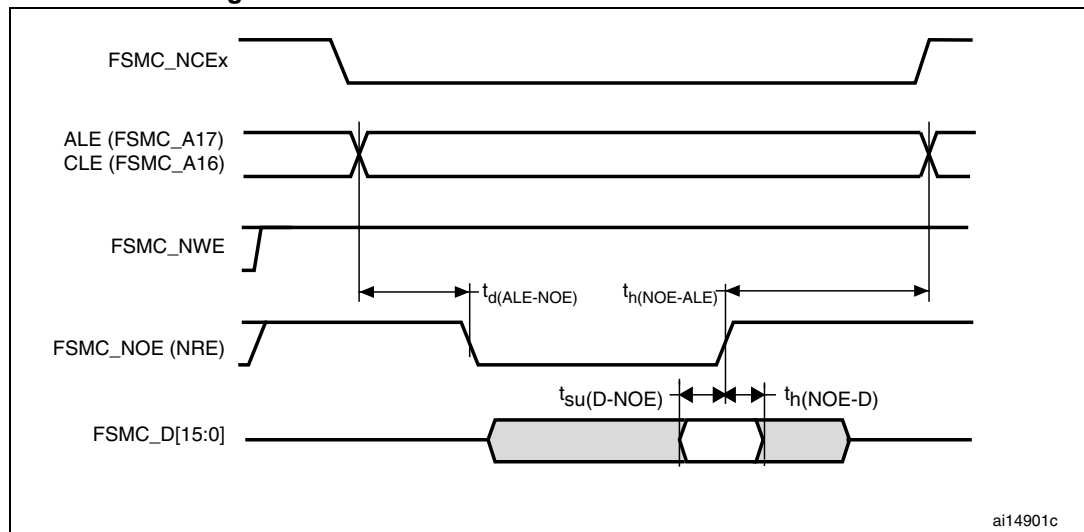


Figure 70. NAND controller waveforms for write access

